

- 10 -

**Amendments to the Abstract:****Please amend the abstract as follows:****Abstract**

B17

On a substrate made of e.g., sapphire single crystal is formed an Al underlayer having a crystallinity FWHM X-ray rocking curve value of 90 seconds or below in FWHM of X-ray rocking curve. Then, ~~on the AlN underlayer is formed a~~ buffer layer is formed on the AlN underlayer and has having a composition of  $\text{Al}_p\text{Ga}_q\text{In}_{1-p-q}\text{N}$  ( $0 \leq p \leq 1$ ,  $0 \leq y \leq q$ ), ~~and a GaN-based semiconductor layer group is formed on the buffer layer, is formed a GaN-based semiconductor layer group:~~